

Appl. No. 09/902,056  
Amdt. dated July 21, 2003  
Reply to Office Action of April 23, 2003

Amendments to the Claims

Claims 10-18 (*Cancelled*)

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26. (*Previously Added*) A wafer, comprising:  
a substrate;

a porous layer comprised of a nanoporous material deposited on the substrate, the porous layer including a low density portion closer to the substrate than a high density portion, the high density portion being a densified form of the low density portion; and

a cap layer deposited on the porous layer in contact with the high density portion, the cap layer including an oxide-based material.

27. (*Previously Added*) The wafer of claim 26, wherein the cap layer includes a Plasma Enhanced Chemical Vapor Deposition (PECVD) oxide layer.

Claims 28-31 (*Cancelled*)

32. (*Currently Amended*) ~~An apparatus~~ A device, comprising:

a wafer including a substrate; and

a layer of a nanoporous material deposited on the substrate, the layer including a low density portion closer to the substrate than a high density portion, the high density portion being a densified form of the low density portion.

33. (*Currently Amended*) ~~The apparatus~~ The device of claim 32, further comprising a cap layer deposited on the high density portion, the cap layer including an oxide-based material.

34. (*Currently Amended*) ~~The apparatus~~ The device of claim 33, wherein the cap layer includes a Plasma Enhanced Chemical Vapor Deposition (PECVD) oxide layer.

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35. (*Currently Amended*) ~~The apparatus~~ The device of claim 32, wherein the low density portion of the layer is in contact with the substrate.

36. (*Currently Amended*) ~~The apparatus~~ The device of claim 32, wherein the layer is comprised of silicon dioxide.

37. (*Withdrawn*) The apparatus of claim 32, further comprising:

a deposition chamber, the wafer being positioned in the deposition chamber; and  
a plasma generator operable to generate a plasma within the deposition chamber to provide the densified form of the low density portion of the layer.

38. (*Withdrawn*) The apparatus of claim 37, wherein the plasma generator includes means for generating a high density plasma stream of Argon ions.

39. (*Withdrawn*) The apparatus of claim 37, further comprising a processor and memory operatively coupled to the plasma generator to control the plasma generator.

40. (*Withdrawn*) The apparatus of claim 39, wherein the plasma generator includes means for generating a high density plasma stream of Argon ions.